



Semiconductor, Inc.

# Ei 16LC05 thru Ei16LC15 Low Capacitance, Bidirectional, Eight Line Monolithic TVS Diode Network

### FEATURES:

- 500 watts Peak Pulse Power ( $t_p = 8 \times 20 \mu s$ )
- ESD and Transient protection for data, signal, and Vcc bus to IEC 1000-4-2, IEC 1000-4-4, IEC 1000-4-5
- Protects up to 8 bi-directional lines
- Standoff voltages from 5 to 15 V
- Low capacitance for high speed interfaces
- Low clamping voltage
- ESD protection >8KV (contact)

**DESCRIPTION** The Ei16LC series of monolithic transient voltage suppressors are designed for applications where voltage transients, caused by electrostatic discharge (ESD) and other induced voltage surges, can permanently damage voltage sensitive components. These TVS diodes are characterized by their high surge capability, extremely fast response time and low on-resistance. The Ei16LC series consists of bi-directional diode arrays with low input capacitances and is specifically designed to protect multiple or single data lines with each channel being electrically independent for multiple I/O port protection. These monolithic diode array networks can be used to protect combinations of 8 unidirectional or bi-directional lines. They provide ESD and surge protection for sensitive power and I/O ports.

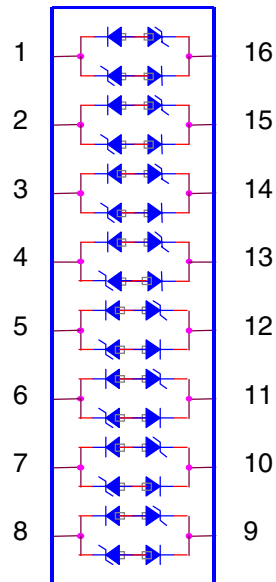
### Applications:

- ESD & surge protection for power lines & I/O ports
- TTL and MOS Bus Lines
- RS-232, Rs-422 and RS-485 data lines
- High speed logic
- High speed data & video transmission

### MECHANICAL CHARACTERISTICS:

- Available in 16 lead SOIC and PDIP
- Solder temperature : 265°C for 10 seconds

### Schematic:



### MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Peak Pulse Power ( $t_p = 8 \times 20 \mu s$ )	Ppk	500	Watts
Operating Temperature	Tj	-55 to +150	°C

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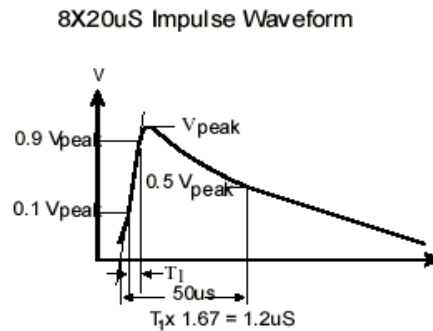
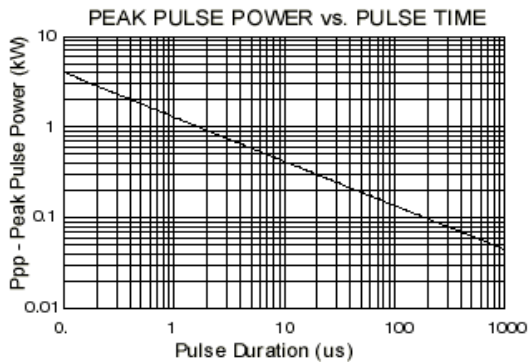
**Ei 16LC05 thru Ei16LC15**  
 Low Capacitance, Bidirectional, Eight  
 Line  
 Monolithic TVS Diode Network

Storage Temperature	Tstg	-55 to +150	°C
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**ELECTRICAL CHARACTERISTICS @ 25°C**

	Reverse Stand-off Voltage	Min Vbr @ 1mA	Max Clamping Voltage @ Ipp=1A	Max Clamping Voltage @ Ipp = 10A	Leakage Current @ VRWM	Max. Cap. @ 0V, 1Mhz
	VRWM	BV(min)	Vc	Vc	IR	Cj
	Volts	Volts	Volts	Volts	µA	pf
Ei16LC05C	5	6	9.8	12.5	400	15
Ei16LC08C	8	8.5	13.4	16.6	10	15
Ei16LC12C	12	13.3	19.0	23.5	2	15
Ei16LC15C	15	16.7	25.5	29.5	2	15

Note : Clamping voltage values are based upon an industry standard 8 x 20µs peak pulse current (Ipp) waveform.



IEC 1000-4-2 ESD WAVEFORM & DISCHARGE PARAMETERS

The graph shows a current impulse waveform. The y-axis is current (I) and the x-axis is time (t). Key parameters are labeled: Ipeak (peak current), 100% (peak), 90% (90% of peak), I at 30nS (current at 30ns), 10% (10% of peak), 30nS (time to 90% of peak), 60nS (time to 10% of peak), and tr = 0.7 to 1 nS (rise time).

Level	First Peak Current (A)	Peak Current at 30ns (A)	Peak Current at 60ns (A)	Test Voltage (Contact Discharge) (kV)	Test Voltage (Air Discharge) (kV)
1	7.5	4	8	2	2
2	15	8	4	4	4
3	22.5	12	6	6	8
4	30	16	8	8	15